

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	100	V
Gate-Source Voltage			V _{GSS}	±20	V
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	I _D	2.9 2.3	A
	t < 10s	T _A = +25°C T _A = +70°C	I _D	3.4 2.7	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	10	A
Maximum Body Diode Continuous Current			I _S	2.5	A
Avalanche Current (Note 7)			I _{AS}	4.7	A
Avalanche Energy (Note 7)			E _{AS}	16	mJ

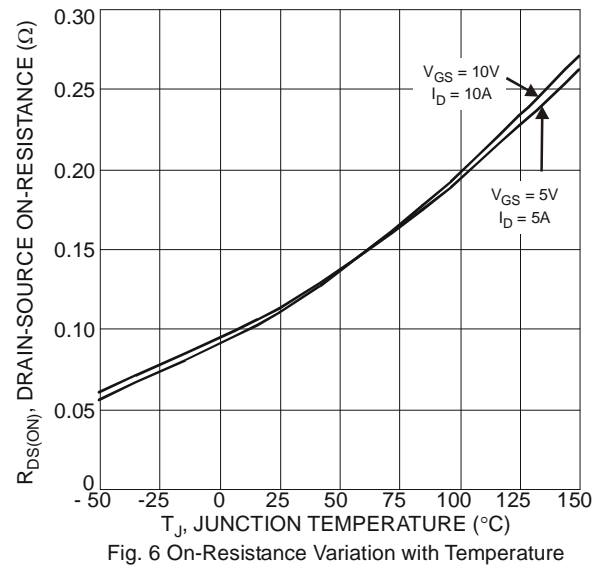
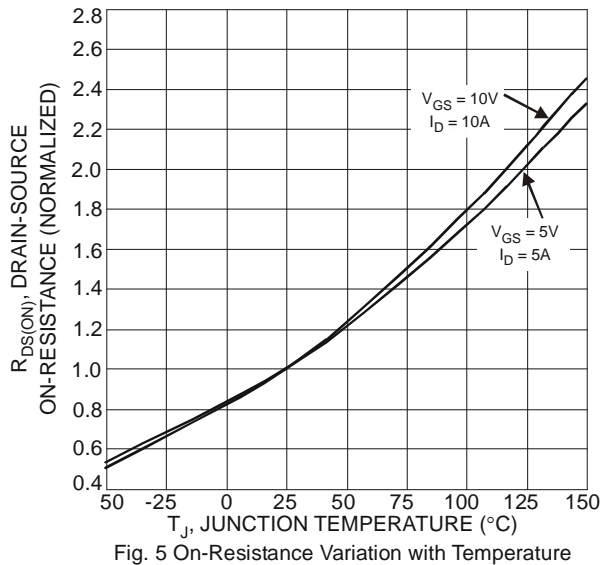
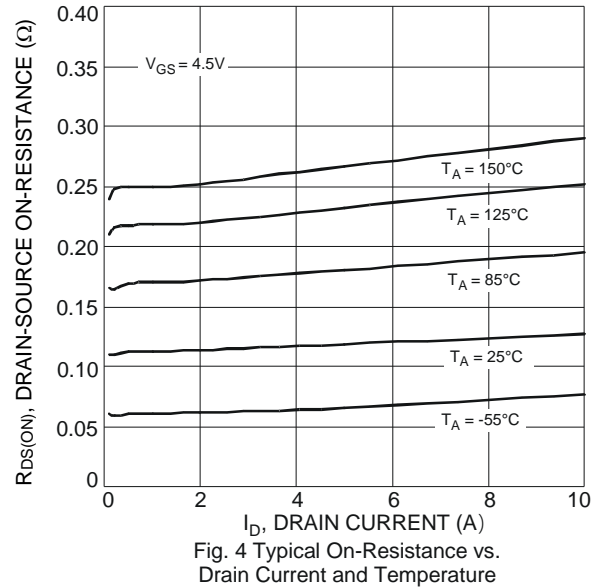
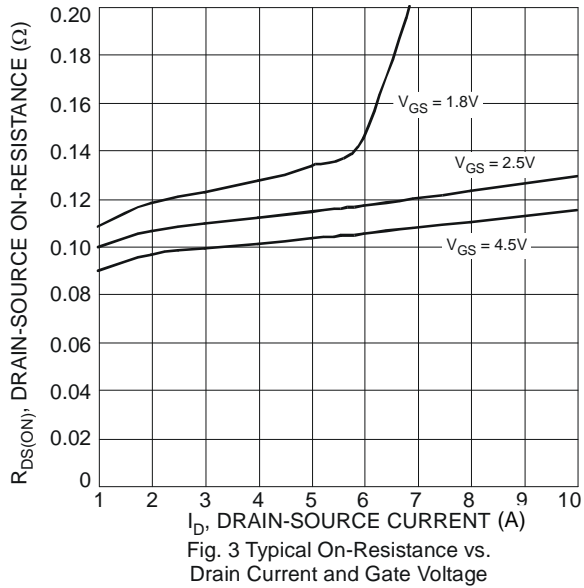
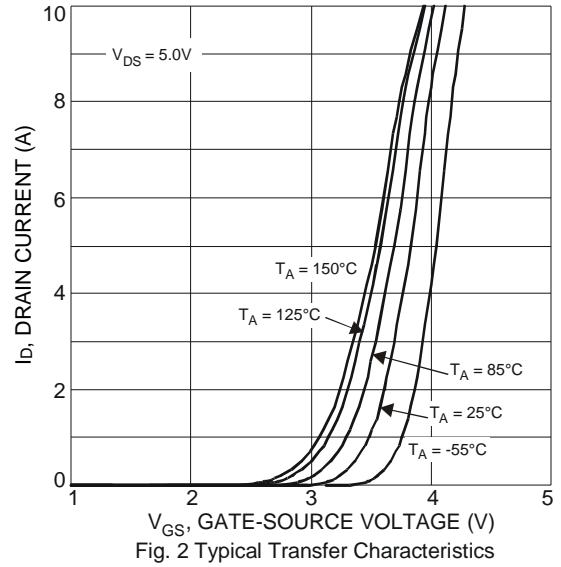
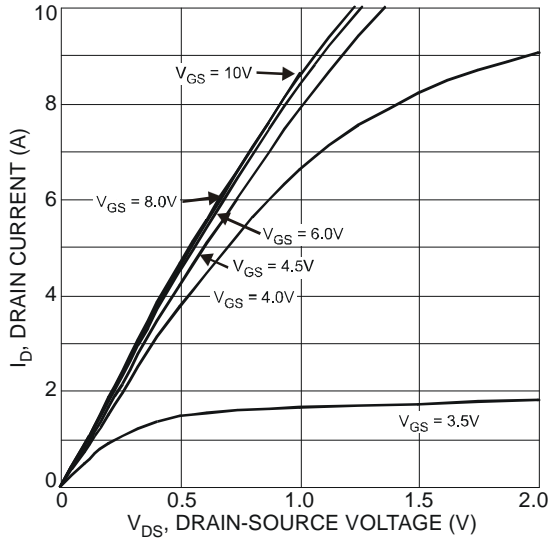
Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	0.66	W
	T _A = +70°C		0.42	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	189	°C/W
	t < 10s		132	
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.03	W
	T _A = +70°C		1.31	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	61	°C/W
	t < 10s		43	
Thermal Resistance, Junction to Case (Note 6)		R _{θJC}	9.3	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—	—	V	V _{GS} = 0V, I _D = 250µA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	1	µA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	1.0	2.0	3.0	V	V _{DS} = V _{GS} , I _D = 250µA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	116	160	mΩ	V _{GS} = 10V, I _D = 5.0A
			126	200		V _{GS} = 4.5V, I _D = 5.0A
Diode Forward Voltage	V _{SD}	—	0.9	1.0	V	V _{GS} = 0V, I _S = 10A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	1167	—	pF	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	36	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	25	—	pF	
Gate Resistance	R _g	—	1.3	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = 4.5V)	Q _g	—	4.9	—	nC	V _{DS} = 80V, I _D = 12.8A
Total Gate Charge (V _{GS} = 10V)	Q _g	—	9.7	—	nC	
Gate-Source Charge	Q _{gs}	—	2.0	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.0	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	10.5	—	ns	V _{DS} = 50V, I _D = 12.8A V _{GS} = 10V, R _G = 25Ω
Turn-On Rise Time	t _R	—	11.1	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	42.6	—	ns	
Turn-Off Fall Time	t _F	—	12.8	—	ns	I _F = 12.8A, di/dt = 100A/µs
Reverse Recovery Time	t _{RR}	—	30.3	—	ns	
Reverse Recovery Charge	Q _{RR}	—	35.2	—	nC	

- Notes:
- Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 - UIS in production with L = 1.43mH, T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.



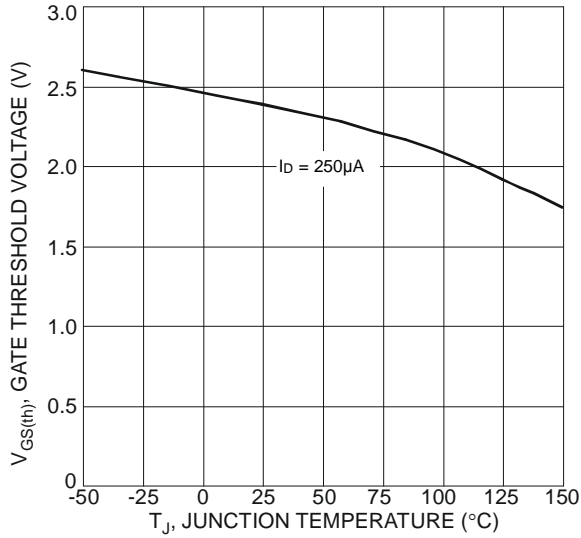


Fig. 7 Gate Threshold Variation vs. Junction Temperature

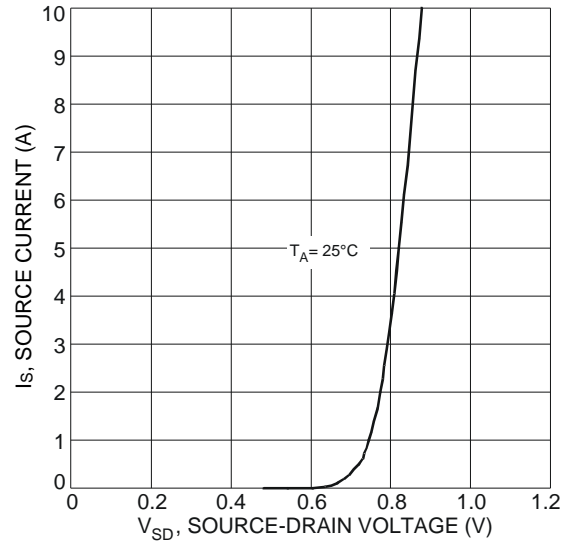


Fig. 8 Diode Forward Voltage vs. Current

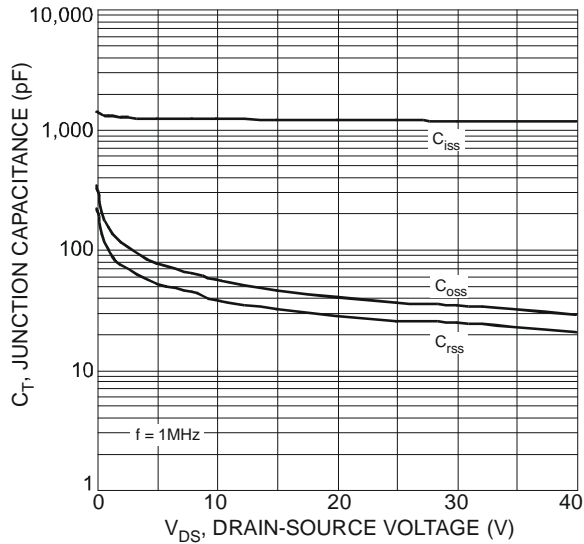


Fig. 9 Typical Junction Capacitance

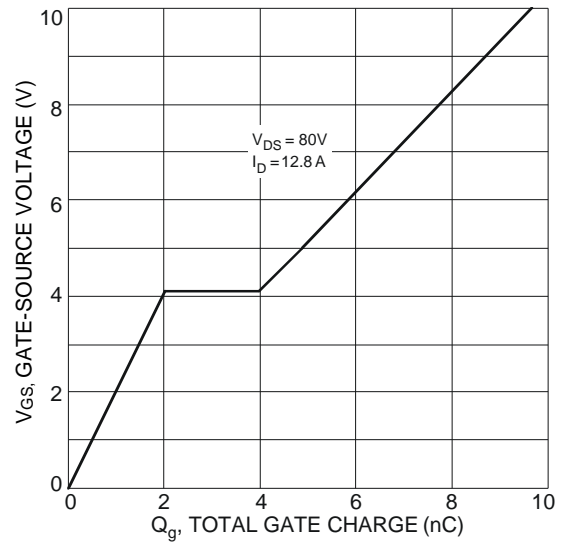


Fig. 10 Gate Charge

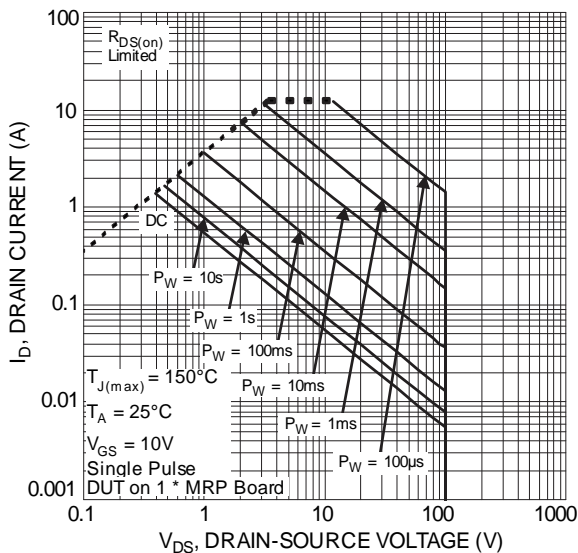
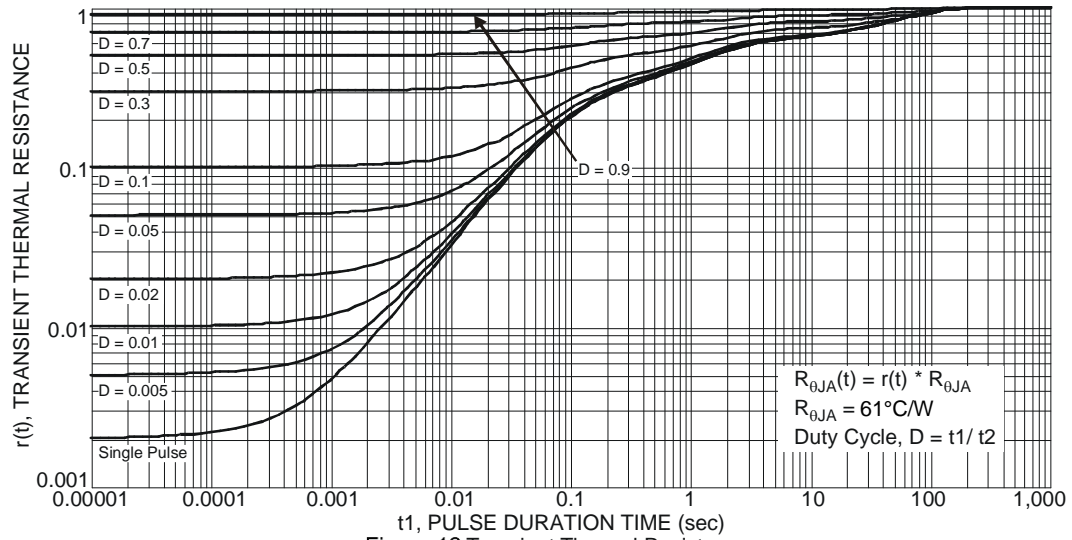


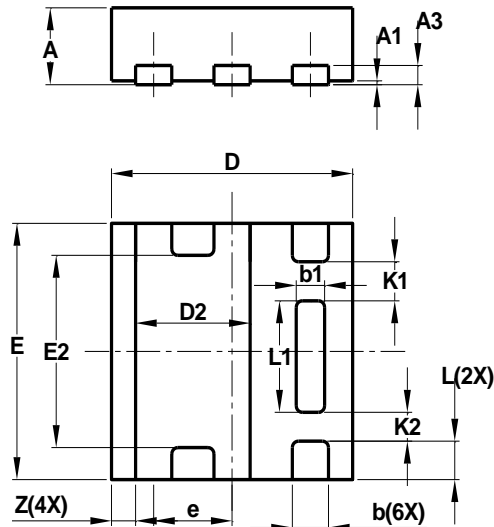
Figure 11 SOA, Safe Operation Area



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type E)

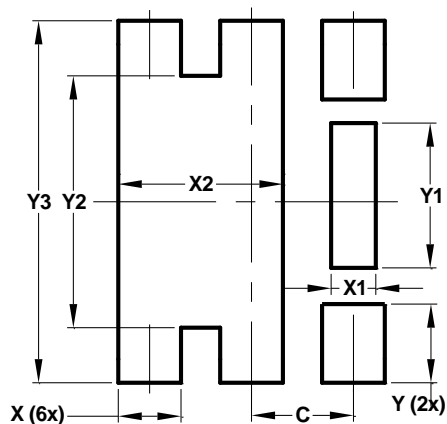


U-DFN2020-6 Type E			
Dim	Min	Max	Typ
A	0.57	0.63	0.60
A1	0	0.05	0.03
A3	—	—	0.15
b	0.25	0.35	0.30
b1	0.185	0.285	0.235
D	1.95	2.05	2.00
D2	0.85	1.05	0.95
E	1.95	2.05	2.00
E2	1.40	1.60	1.50
e	—	—	0.65
L	0.25	0.35	0.30
L1	0.82	0.92	0.87
K1	—	—	0.305
K2	—	—	0.225
Z	—	—	0.20
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-DFN2020-6 (Type E)



Dimensions	Value (in mm)
C	0.650
X	0.400
X1	0.285
X2	1.050
Y	0.500
Y1	0.920
Y2	1.600
Y3	2.300

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